

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- BLDC Motor driver
- DC-DC
- Battery protection

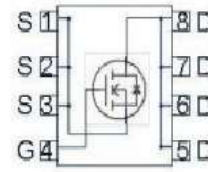
Ordering Information:

Part NO.	ZMS008N04NC
Marking	ZMS008N04
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

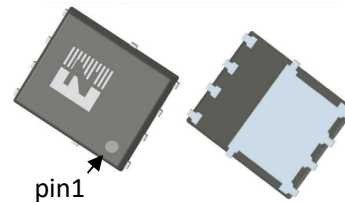
Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}\text{C}$	310	A
	I_D	$T_C=75^{\circ}\text{C}$	238	A
	I_D	$T_C=100^{\circ}\text{C}$	194	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^{\circ}\text{C}$;	930	A
Total Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$	139	W
Total Power Dissipation	P_D	$T_A=25^{\circ}\text{C}$	3.5	W
Operating Junction Temperature	T_J		-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}		-55 to +150	$^{\circ}\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	320	mJ
		$L=0.5\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	680	mJ
ESD Level (HBM)	CLASS 2			

Product Summary



$V_{DS} = 40\text{V}$
 $R_{DS(ON)} = 0.7\text{m}\Omega$
 $I_D = 310\text{A}$



DFN5*6



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.9	°C/W
Thermal resistance, junction-ambient	$R_{thJA①}$		-	36	°C/W
Soldering temperature	T_{sld}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.6	1.9	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$		0.7	0.91	m Ω
		$V_{GS}=4.5V, I_D=30A$		1.0	1.8	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$		30		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=40A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	6250	-	pF
Output capacitance	C_{oss}		-	1760	-	
Reverse transfer capacitance	C_{rss}		-	100	-	
Gate Resistance	R_g	$f=1MHz$	-	1.6	-	Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	104	-	nC
Gate - Source charge	Q_{gs}		-	11	-	
Gate - Drain charge	Q_{gd}		-	32	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	23	-	ns
Turn-ON Rise time	t_r		-	26	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	65	-	ns
Turn-Off Fall time	t_f		-	17	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, dI_S/dt=100A/\mu s, I_S=50A$	-	65	-	ns
Reverse Recovery Charge	Q_{RR}		-	95	-	nC

Fig.1 Gate-Charge Characteristics

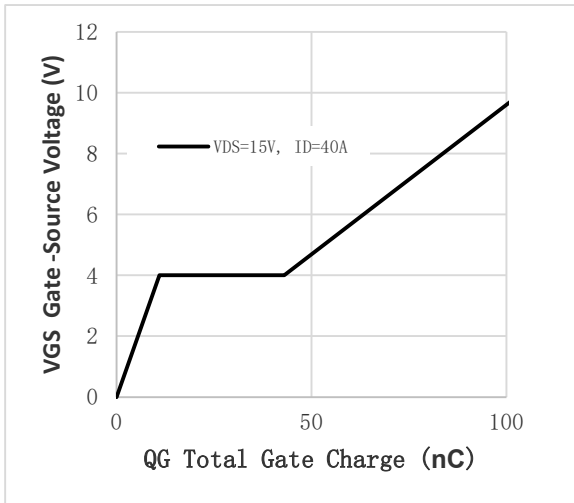


Fig.2 Capacitance Characteristics

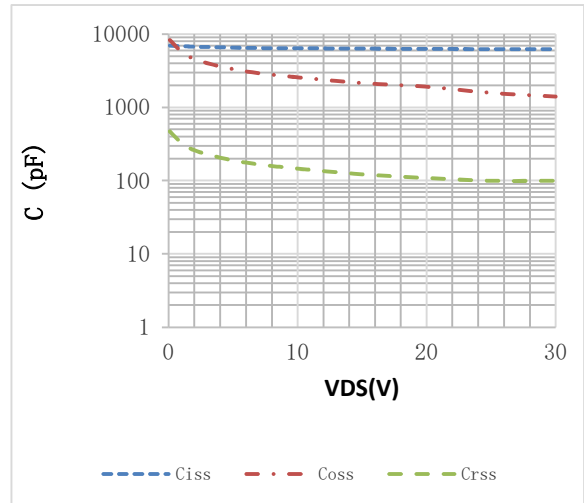


Fig.3 Power Dissipation

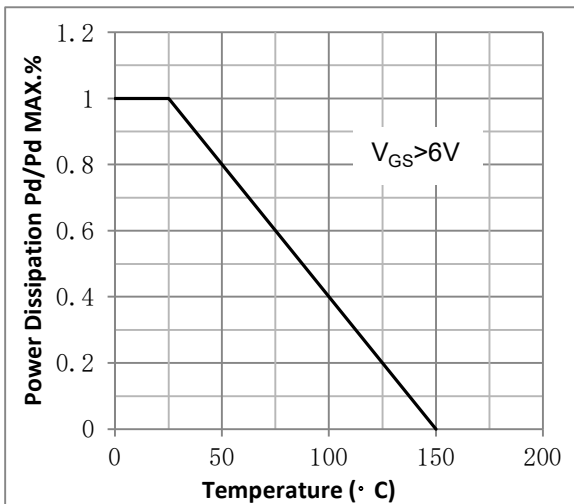


Fig.4 Typical output Characteristics

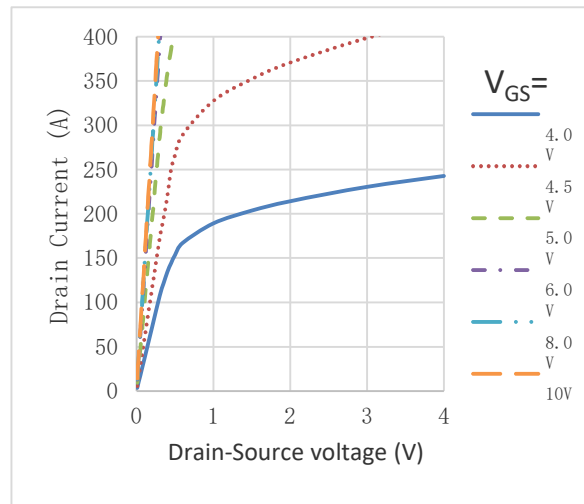


Fig.5 Threshold Voltage V.S Junction Temperature

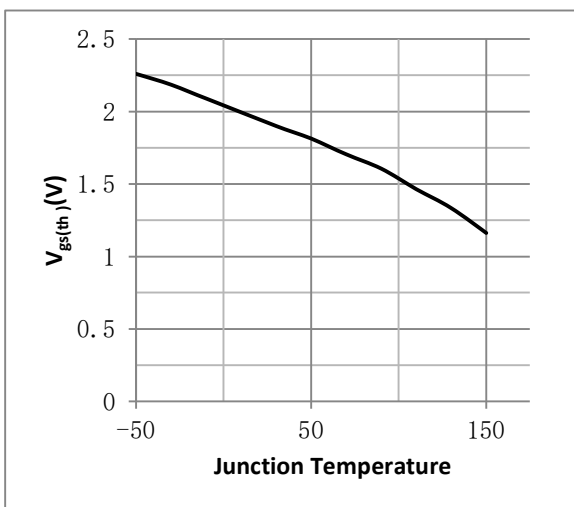


Fig.6 Resistance V.S Drain Current

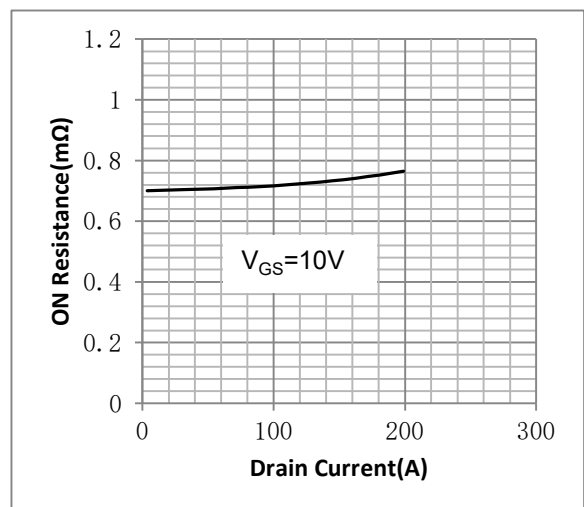


Fig.7 On-Resistance VS Gate Source Voltage

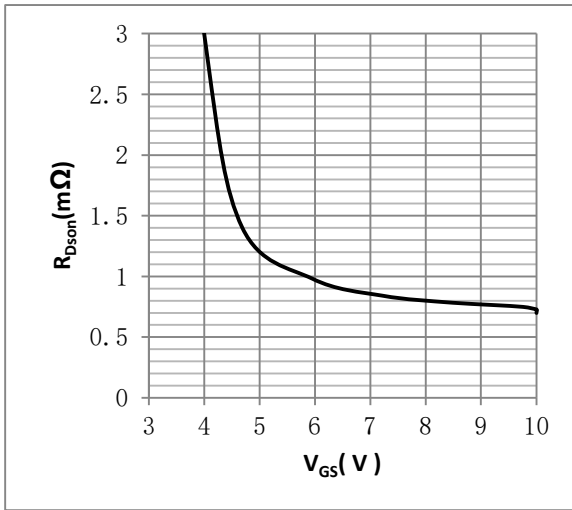


Fig.8 On-Resistance V.S Junction Temperature

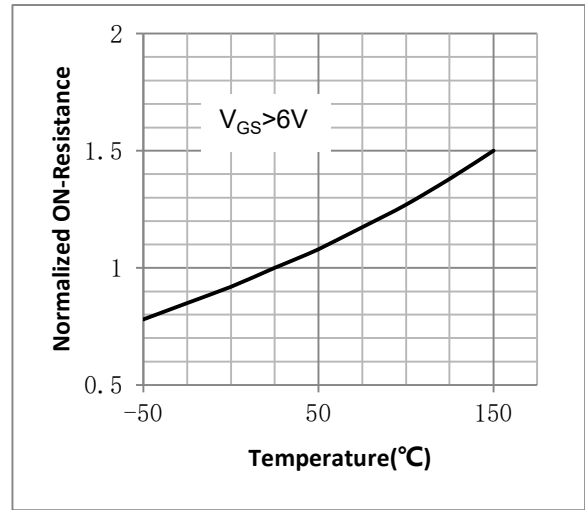


Figure 9. Diode Forward Voltage vs. Current

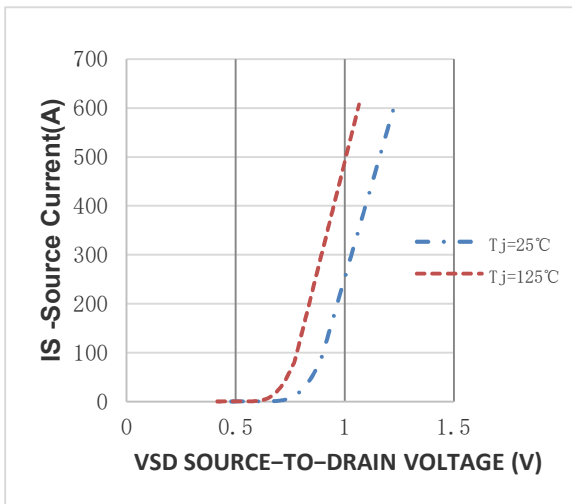


Figure 10. Transfer Characteristics

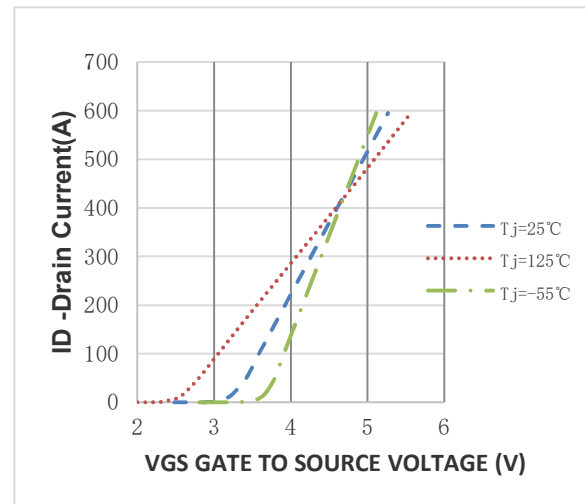


Fig.11 Safe Operating Area

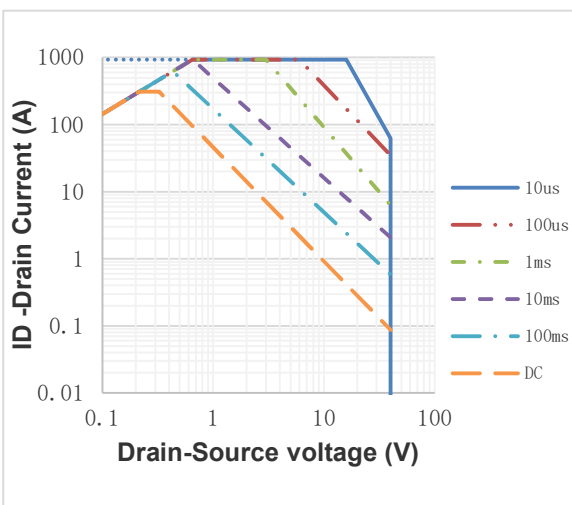
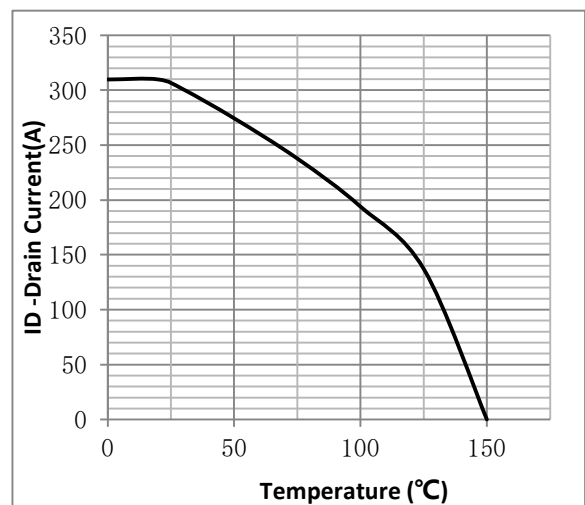
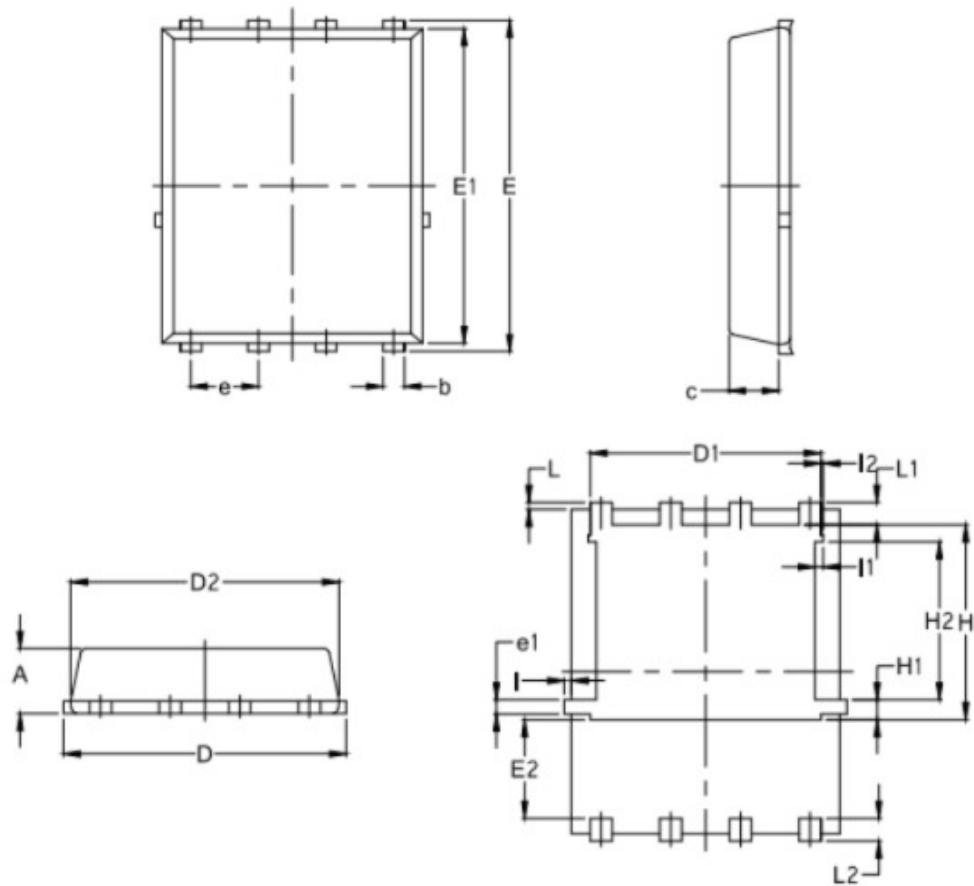


Fig.12 I_D vs. Case Temperature^②



•DFN5*6 Package Outline



DIM	MILLIMETERS		
	MIN.	MOM.	MAX.
A	0.90	1.00	1.10
b	0.34	0.41	0.48
c	0.82	0.89	0.97
D	4.80	5.10	5.40
D1	4.10	4.20	4.31
D2	4.80	4.90	5.00
E	5.95	6.05	6.15
E1	5.65	5.75	5.85
E2	1.10		-
e	1.27 BSC		
L	0.05	0.15	0.25
L1	0.38	0.44	0.50
L2	0.38	0.44	0.50
H	3.30	3.40	3.50
I	-		0.18
I1	-		0.15
I2	-		0.038
H1	0.33	0.34	0.35
H2	2.75	2.80	2.85
e1	0.25 BSC		

Note:

① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

② Practically the current will be limited by PCB, thermal design and operating temperature.
VGS=10V.

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Revision History

Version	Date	Change
A	2021.1.15	
B	2021.9.20	1.Add Dynamic characteristic t_f , t_r etc.
C	2022.2.2	1.Add Reach, HF figure, 2.ID modify
D	2024.1.13	Correct characteristic curves